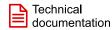


DS90LV011AH







JAJSGS7C - SEPTEMBER 2005 - REVISED JULY 2021



DS90LV011AH 高温対応 3V LVDS 差動ドライバ

1 特長

TEXAS

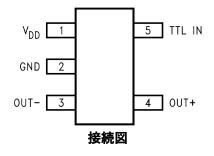
- -40°C~125°Cの動作温度範囲
- TIA/EIA-644-A 規格に準拠

INSTRUMENTS

- 400Mpbs (200MHz) を超えるスイッチング速度
- 最大差動スキュー 700ps (標準値 100ps)
- 最大伝搬遅延 1.5ns
- 3.3V の単一電源
- ±350mV の差動信号
- 電源オフ保護 (TRI-STATE で出力)
- PCB レイアウトを簡素化するピン配置
- 低消費電力 (3.3V 時の標準値 23mW)
- 5ピンの SOT-23 パッケージ
- SN65LVDS1 とピン互換

2 アプリケーション

- 基板間通信
- 試験/測定機器
- モータ・ドライブ
- LED ビデオ・ウォール
- ワイヤレス・インフラ
- 通信インフラ
- 多機能プリンタ
- NIC カード
- ラック・サーバー
- 超音波スキャナ



3 概要

DS90LV011AH は LVDS ドライバで、データ・レートが高 く低消費電力のアプリケーション用に最適化されていま す。DS90LV011AH は電流モード・ドライバで、高い周波 数でも低消費電力を維持できます。さらに、短絡フォルト 時の電流も最小化されています。このデバイスは、低電圧 差動信号 (LVDS) テクノロジを活用し、400Mbps (200MHz) を超えるデータ速度をサポートするよう設計さ れています。

このデバイスは、5 ピンの SOT-23 パッケージで供給され ます。LVDS 出力は、PCB レイアウトが簡単になるよう配 置されています。差動ドライバ出力により電磁気干渉 (EMI) が低く、出力スイングは 350mV (標準値) と小さくな ります。DS90LV011AH は、対になるシングル・ライン・レ シーバ DS90LT012AH や、他の任意の TI 製 LVDS レシ ーバと組み合わせでき、高速な LVDS インターフェイスを 実現できます。

製品情報(1)

部品番号	パッケージ	本体サイズ (公称)
DS90LV011AH	SOT-23 (5)	2.90mm × 1.60mm

利用可能なすべてのパッケージについては、このデータシートの 末尾にある注文情報を参照してください。

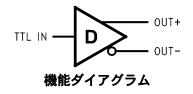




Table of Contents

1 特長	1 8.4 Device Functional Modes	8
2アプリケーション		9
3 概要		9
4 Revision History		9
5 Pin Configuration and Functions		12
6 Specifications	11 Layout	13
6.1 Absolute Maximum Ratings ⁽¹⁾ (2)	11.1 Layout Guidelines	13
6.2 ESD Ratings	11.2 Layout Example	17
6.3 Recommended Operating Conditions		
6.4 Thermal Information		
6.5 Electrical Characteristics	40.0 D N	es18
6.6 Switching Characteristics		
6.7 Typical Characteristics		
7 Parameter Measurement Information		
8 Detailed Description		
8.1 Overview	******	
8.2 Functional Block Diagram		18
8.3 Feature Description		
資料番号末尾の英字は改訂を表しています。その改言 Changes from Revision A (January 2019) to Re		Dogo
<u> </u>	vision C (July 2021) を更新	Page
Corrected pin description table. Pin 3 should be	e OUT- and pin 4 should be OUT+	3
Changes from Revision A (April 2013) to Revisi	ion B (January 2019)	Page
の機能モード」セクション、「アプリケーションと実装	引表、「 <i>代表的特性</i> 」セクション、「 <i>機能説明</i> 」セクション、「デバ 」セクション、「 <i>電源に関する推奨事項</i> 」セクション、「 <i>レイアウト</i> フション、「 <i>メカニカル、パッケージ、および注文情報</i> 」セクション	」セク
加		1
· Changed the Absolute Maximum Ratings tabler	note	4
• Moved the ESD parameters in the Absolute Ma	eximum Ratings table to the ESD Ratings table	4
• Changed the Temperature (T _A) parameter in the	e Recommended Operating Conditions table to Junction	
Changes from Revision * (April 2013) to Revision	on A (April 2012)	Page

Submit Document Feedback

Page

ナショナル セミコンダクターのデータシートのレイアウトを TI 形式に変更.......1



5 Pin Configuration and Functions

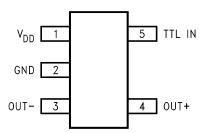


図 5-1. DBV Package 5-Pin SOT-23 Top View

表 5-1. Pin Functions

PIN		I/O	DESCRIPTION		
NO.	NAME	1/0	DESCRIPTION		
1	V _{DD}	I	Power supply pin, +3.3 V ± 0.3 V		
2	GND	I	Ground pin		
3	OUT-	0	Inverting driver output pin		
4	OUT+	0	Noninverting driver output pin		
5	TTL IN	I	LVTTL/LVCMOS driver input pins		



6 Specifications

6.1 Absolute Maximum Ratings⁽¹⁾ (2)

		MIN	MAX	UNIT
Supply voltage (V _{DD})		-0.3	4	V
LVCMOS input voltage (TTL	IN)	-0.3	3.6	V
LVDS output voltage (OUT±)		-0.3	3.9	V
LVDS output short circuit curr		24	mA	
Maximum package power	DBV Package		902	mW
dissipation at +25°C	power DBV Package		7.22	mW/°C
Lead temperature range soldering (4 sec.)			260	°C
Maximum Junction Temperature			150	°C
Storage temperature, T _{stg}		-65	150	°C

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability

6.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 $^{(1)}$ (1.5 k Ω , 100 pF)	9000	
V _(ESD) Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾ (0 Ω, 0 pF)		V	
		EIAJ (0 Ω, 200 pF)	900	
		IEC direct (330 Ω, 150 pF)	4000	

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Pins listed as ±9000 V may actually have higher performance.

6.3 Recommended Operating Conditions

	MIN	NOM	MAX	UNIT
Supply voltage (V _{DD})	3	3.3	3.6	V
Junction temperature (T _A)	-40	+25	+125	°C
Junction temperature (T _J)			+130	°C

6.4 Thermal Information

		DS90LV011AH	
	THERMAL METRIC ⁽¹⁾	DBV (SOT-23)	UNIT
		5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	177.7	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	104.4	°C/W
R _{θJB}	Junction-to-board thermal resistance	43.5	°C/W
ΨЈТ	Junction-to-top characterization parameter	19.3	°C/W
ΨЈВ	Junction-to-board characterization parameter	43.2	°C/W

⁽¹⁾ For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

Product Folder Links: DS90LV011AH

⁽²⁾ If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/Distributors for availability and specifications.

⁽²⁾ JJEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Pins listed as ±2000 V may actually have higher performance.

6.5 Electrical Characteristics

over Supply Voltage and Operating Temperature ranges, unless otherwise specified. (1) (2) (3)

	PARAMETER	TEST	CONDITIONS	PIN	MIN	TYP	MAX	UNIT
V _{OD}	Output Differential Voltage	R _L = 100 Ω	⊣ -		250	350	450	mV
ΔV_{OD}	V _{OD} Magnitude Change	(図 7-1 and 図 7	7-2)			3	35	mV
Vos	Offset Voltage	R _L = 100 Ω			1.125	1.22	1.375	V
ΔV _{OS}	Offset Magnitude Change	(図 7-1)	- ⁻		0	1	25	mV
I _{OFF}	Power-off Leakage	V _{OUT} = 3.6 V or	GND, V _{DD} = 0 V	OUT+,		±1	±10	μA
Ios	Output Short Circuit Current(4)	V _{OUT+} and V _{OUT}	_{r-} = 0 V			-6	-24	mA
I _{OSD}	Differential Output Short Circuit Current ⁽⁴⁾	V _{OD} = 0 V	V _{OD} = 0 V			-5	-12	mA
C _{OUT}	Output Capacitance					3		pF
V _{IH}	Input High Voltage				2		V_{DD}	V
V _{IL}	Input Low Voltage				GND		0.8	V
I _{IH}	Input High Current	V _{IN} = 3.3 V or 2	.4 V	TTL IN		±2	±10	μA
I _{IL}	Input Low Current	V _{IN} = GND or 0.	V _{IN} = GND or 0.5 V			±1	±10	μA
V _{CL}	Input Clamp Voltage	I _{CL} = −18 mA	I _{CL} = −18 mA		-1.5	-0.6		V
C _{IN}	Input Capacitance					3		pF
	Power Supply Current	No Load	V = V or GND	V _{DD}		5	8	mA
I _{DD}	i ower Suppry Guiterit	R _L = 100 Ω	$R_L = 100 \Omega$ $V_{IN} = V_{DD} \text{ or GND}$			7	10	mA

⁽¹⁾ Current into device pins is defined as positive. Current out of device pins is defined as negative. All voltages are referenced to ground except V_{OD}.

- (2) All typicals are given for: $V_{DD} = +3.3V$ and $T_A = +25$ °C.
- (3) The DS90LV011AH is a current mode device and only function with datasheet specification when a resistive load is applied to the drivers outputs.
- (4) Output short circuit current (I_{OS}) is specified as magnitude only, minus sign indicates direction only.

6.6 Switching Characteristics

Over Supply Voltage and Operating Temperature Ranges, unless otherwise specified. (1) (2) (3) (4)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PHLD}	Differential Propagation Delay High to Low		0.3	1	1.5	ns
t _{PLHD}	Differential Propagation Delay Low to High		0.3	1.1	1.5	ns
t _{SKD1}	Differential Pulse Skew t _{PHLD} - t _{PLHD} ⁽⁵⁾		0	0.1	0.7	ns
t _{SKD3}	Differential Part to Part Skew ⁽⁶⁾	$R_L = 100\Omega$, $C_L = 15 pF$	0	0.2	1	ns
t _{SKD4}	Differential Part to Part Skew ⁽⁷⁾	(⊠ 7-3 and ⊠ 7-4)	0	0.4	1.2	ns
t _{TLH}	Transition Low to High Time		0.2	0.5	1	ns
t _{THL}	Transition High to Low Time		0.2	0.5	1	ns
f _{MAX}	Maximum Operating Frequency ⁽⁸⁾		200	250		MHz

⁽¹⁾ All typicals are given for: $V_{DD} = +3.3V$ and $T_A = +25$ °C.

- (3) C₁ includes probe and fixture capacitance.
- (4) Generator waveform for all tests unless otherwise specified: f = 1 MHz, $Z_0 = 50\Omega$, $t_r \le 1 \text{ ns}$, $t_f \le 1 \text{ ns}$ (10%-90%).
- (5) t_{SKD1} , $|t_{PHLD} t_{PLHD}|$, is the magnitude difference in differential propagation delay time between the positive going edge and the negative going edge of the same channel.
- (6) t_{SKD3}, Differential Part to Part Skew, is defined as the difference between the minimum and maximum specified differential propagation delays. This specification applies to devices at the same V_{DD} and within 5°C of each other within the operating temperature range.
- (7) t_{SKD4}, part to part skew, is the differential channel to channel skew of any event between devices. This specification applies to devices over recommended operating temperature and voltage ranges, and across process distribution. t_{SKD4} is defined as |Max Min| differential propagation delay.

Copyright © 2022 Texas Instruments Incorporated

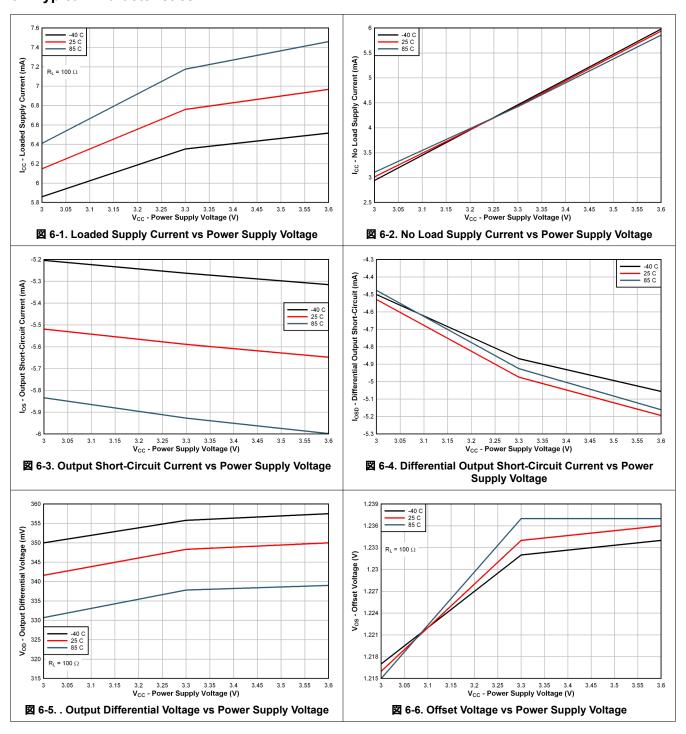
Submit Document Feedback

⁽²⁾ These parameters are specified by design. The limits are based on statistical analysis of the device performance over PVT (process, voltage, temperature) ranges.



(8) f_{MAX} generator input conditions: t_r = t_f < 1 ns (0% to 100%), 50% duty cycle, 0V to 3V. Output criteria: duty cycle = 45%/55%, V_{OD} > 250mV. The parameter is specified by design. The limit is based on the statistical analysis of the device over the PVT range by the transitions times (t_{TLH} and t_{THL}).

6.7 Typical Characteristics





7 Parameter Measurement Information

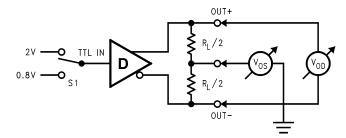


図 7-1. Differential Driver DC Test Circuit

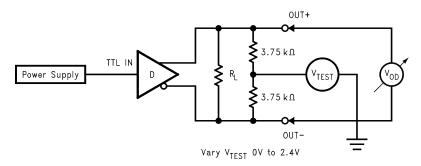


図 7-2. Differential Driver Full Load DC Test Circuit

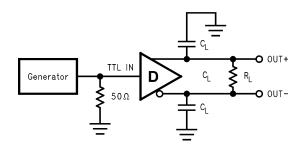
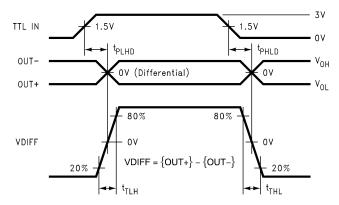


図 7-3. Differential Driver Propagation Delay and Transition Time Test Circuit



☑ 7-4. Differential Driver Propagation Delay and Transition Time Waveforms

Copyright © 2022 Texas Instruments Incorporated

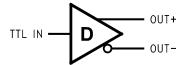
8 Detailed Description

8.1 Overview

The DS90LV011AH is a single-channel, low-voltage differential signaling (LVDS) line driver with a balanced current source design. It operates from a single supply that is nominally 3.3 V, but can be as low as 3.0 V and as high as 3.6 V. The input signal to the DS90LV011AH is an LVCMOS/LVTTL signal. The output of the device is a differential signal complying with the LVDS standard (TIA/EIA-644). The differential output signal operates with a signal level of 350 mV, nominally, at a common-mode voltage of 1.2 V. This low differential output voltage results in low electromagnetic interference (EMI). The differential nature of the output provides immunity to common-mode coupled signals that the driven signal may experience.

The DS90LV011AH is primarily used in point-to-point configurations, as seen in \boxtimes 9-1. This configuration provides a clean signaling environment for the fast edge rates of the DS90LV011AH and other LVDS drivers. The DS90LV011AH is connected through a balanced media which may be a standard twisted pair cable, a parallel pair cable, or simply PCB traces to a LVDS receiver. Typically, the characteristic differential impedance of the media is in the range of 100 Ω . The DS90LV011AH device is intended to drive a 100- Ω transmission line. The 100- Ω termination resistor is selected to match the media and is located as close to the LVDS receiver input pins as possible.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 DS90LV011AH Driver Functionality

As can be seen in $\frac{1}{2}$ 8-1, the driver signle-ended input to differential output relationship is defined. When the driver input is left open, the differential output is undefined.

20 11 2000 2101 17 11 211101 1 4110110114111,						
INPUT	OUTPUTS					
LVCMOS/LVTTL IN	OUT +	OUT -				
Н	Н	L				
L	L	Н				
Open	?	?				

表 8-1. DS90LV011AH Driver Functionality

8.3.2 Driver Output Voltage and Power-On Reset

The DS90LV011AH driver operates and meets all the specified performance requirements for supply voltages in the range of 3.0 V to 3.6 V. When the supply voltage drops below 1.5 V (or is turning on and has not yet reached 1.5 V), power-on reset circuitry set the driver output to a high-impedance state.

8.3.3 Driver Offset

An LVDS-compliant driver is required to maintain the common-mode output voltage at 1.2 V (±75 mV). The DS90LV011AH incorporates sense circuitry and a control loop to source common-mode current and keep the output signal within specified values. Further, the device maintains the output common-mode voltage at this set point over the full 3.0-V to 3.6-V supply range.

8.4 Device Functional Modes

The device has one mode of operation that applies when operated within セクション 6.3.

9 Application and Implementation

Note

以下のアプリケーション情報は、TIの製品仕様に含まれるものではなく、TIではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

9.1 Application Information

The DS90LV011AH device is a single-channel LVDS driver. The functionality of this device is simple, yet extremely flexible, leading to its use in designs ranging from wireless base stations to desktop computers. The varied class of potential applications share features and applications discussed in the paragraphs below. The DS90LV011AH has a flow-through pinout that allows for easy PCB layout. The LVDS signals on one side of the device easily allows for matching electrical lengths of the differential pair trace lines between the driver and the receiver as well as allowing the trace lines to be close together to couple noise as common-mode. Noise isolation is achieved with the LVDS signals on one side of the device and the TTL signals on the other side.

9.2 Typical Application

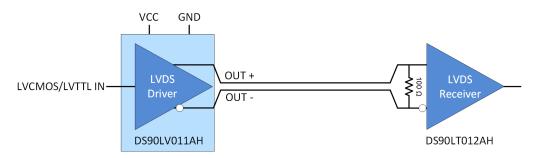


図 9-1. Point-to-Point Application

9.2.1 Design Requirements

表 9-1 lists the design parameters for this example

DESIGN PARAMETERS	EXAMPLE VALUE				
Driver Supply Voltage (V _{DD})	3 to 3.6 V				
Driver Input Voltage	0 to V _{DD}				
Signaling Rate	0 to 400 Mbps				
Interconnect Characteristic Impedance	100 Ω				
Number of Receiver Nodes	1				
Ground shift between driver and receiver	±1 V				

表 9-1. Design Parameters

9.2.2 Detailed Design Procedure

9.2.2.1 Driver Supply Voltage

DS90LV011AH is a LVDS that is operated from a single supply. The device can support operation with a supply as low as 3.0 V and as high as 3.6 V. The driver output voltage is dependent upon the chosen supply voltage. The minimum output voltage stays within the specified LVDS limits (247 mV to 450 mV) for a 3.3-V supply. If the supply range is between 3.0 V and 3.6 V, the minimum output voltage may be as low as 150 mV. If a communication link is designed to operate with a supply within this lower range, the channel noise margin will need to be looked at carefully to ensure error-free operation.

9.2.2.2 Driver Bypass Capacitance

Bypass capacitors play a key role in power distribution circuitry. Specifically, they create low-impedance paths between power and ground. At low frequencies, a good digital power supply offers very low-impedance paths between its terminals. However, as higher frequency currents propagate through power traces, the source is quite often incapable of maintaining a low-impedance path to ground. Bypass capacitors are used to address this shortcoming. Usually, large bypass capacitors (10 μ F to 1000 μ F) at the board-level do a good job up into the kHz range. Due to their size and length of their leads, they tend to have large inductance values at the switching frequencies of modern digital circuitry. To solve this problem, one must resort to the use of smaller capacitors (nF to μ F range) installed locally next to the integrated circuit.

Multilayer ceramic chip or surface-mount capacitors (size 0603 or 0805) minimize lead inductances of bypass capacitors in high-speed environments, because their lead inductance is about 1 nH. For comparison purposes, a typical capacitor with leads has a lead inductance around 5 nH.

The value of the bypass capacitors used locally with LVDS chips can be determined by ± 1 and ± 2 according to Johnson¹ equations 8.18 to 8.21. A conservative rise time of 200 ps and a worst-case change in supply current of 1 A covers the whole range of LVDS devices offered by Texas Instruments. In this example, the maximum power supply noise tolerated is 200 mV. However, this figure varies depending on the noise budget available in the design. ¹

$$C_{\text{chip}} = \left(\frac{\Delta I_{\text{Maximum Step Change Supply Current}}}{\Delta V_{\text{Maximum Power Supply Noise}}}\right) \times T_{\text{Rise Time}} \tag{1}$$

$$C_{\text{LVDS}} = \left(\frac{1A}{0.2V}\right) \times 200 \text{ ps} = 0.001 \,\mu\text{F} \tag{2}$$

 \boxtimes 9-2 lowers lead inductance and covers intermediate frequencies between the board-level capacitor (>10 μ F) and the value of capacitance found above (0.001 μ F). TI recommends that the user place the smallest value of capacitance as close to the chip as possible.



図 9-2. Recommended LVDS Bypass Capacitor Layout

9.2.2.3 Driver Input Votlage

DS90LV011AH input is designed to support a wide input voltage range. The input stage can accept signals as high as 3.6 V when the supply voltage is 3.6 V.

9.2.2.4 Driver Output Voltage

DS90LV011AH driver output has a 1.2-V common-mode voltage, with a nominal differential output signal of 350 mV. This 350 mV is the absolute value of the differential swing (VOD = |V+-V-|). The peak-to-peak differential voltage is twice this value, or 700 mV. LVDS receiver thresholds are ± 100 mV. With these receiver decision thresholds, it is clear that the disadvantage of operating the driver with a lower supply will be noise margin. With fully compliant LVDS drivers and receivers, we would expect a minimum of ~ 150 mV of noise margin (247-mV minimum output voltage -100-mV maximum input requirement). If we operate the DS90LV011AH with a supply in the range of 3.0 V to 3.6 V, the minimum noise margin will drop to 150 mV.

Product Folder Links: DS90I V011AH

Howard Johnson & Martin Graham.1993. High Speed Digital Design – A Handbook of Black Magic. Prentice Hall PRT. ISBN number 013395724.

9.2.2.5 Interconnecting Media

The physical communication channel between the driver and the driver may be any balanced and paired metal conductors meeting the requirements of the LVDS standard, the key points of which are included here. This media may be a twisted-pair, twinax, flat ribbon cable, or PCB traces. The nominal characteristic impedance of the interconnect media should be between 100 Ω and 120 Ω with a variation of no more than 10% (90 Ω to 132 Ω).

9.2.2.6 PCB Transmission Lines

As per the LVDS Owner's Manual Design Guide, 4th Edition, 29-3 depicts several transmission line structures commonly used in printed-circuit boards (PCBs). Each structure consists of a signal line and return path with a uniform cross section along its length. A microstrip is a signal trace on the top (or bottom) layer, separated by a dielectric layer from its return path in a ground or power plane. A stripline is a signal trace in the inner layer, with a dielectric layer in between a ground plane above and below the signal trace. The dimensions of the structure along with the dielectric material properties determine the characteristic impedance of the transmission line (also called controlled-impedance transmission line).

When two signal lines are placed close by, they form a pair of coupled transmission lines.

9-3 shows examples of edge-coupled microstrip lines, and edge-coupled or broad-side-coupled striplines. When excited by differential signals, the coupled transmission line is referred to as a differential pair. The characteristic impedance of each line is called odd-mode impedance. The sum of the odd-mode impedances of each line is the differential impedance of the differential pair. In addition to the trace dimensions and dielectric material properties, the spacing between the two traces determines the mutual coupling and impacts the differential impedance. When the two lines are immediately adjacent; for example, S is less than 2 W, the differential pair is called a tightly-coupled differential pair. To maintain constant differential impedance along the length, it is important to keep the trace width and spacing uniform along the length, as well as maintain good symmetry between the two lines.

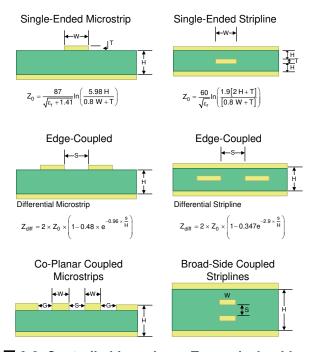


図 9-3. Controlled-Impedance Transmission Lines

9.2.3 Termination Resistor

As shown earlier, an LVDS communication channel employs a current source driving a transmission line that is terminated with a resistive load. This load serves to convert the transmitted current into a voltage at the receiver input. To ensure incident wave switching (which is necessary to operate the channel at the highest signaling rate), the termination resistance should be matched to the characteristic impedance of the transmission line. The designer should ensure that the termination resistance is within 10% of the nominal media characteristic impedance. If the transmission line is targeted for $100-\Omega$ impedance, the termination resistance should be between $90~\Omega$ and $110~\Omega$. The line termination resistance should be placed as close to the receiver as possible to minimize the stub length from the resistor to the receiver.

9.2.4 Application Curve

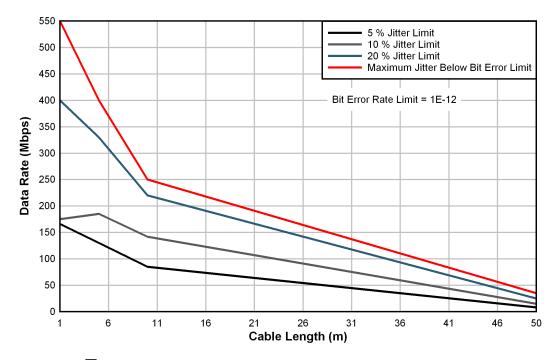


図 9-4. DS90LV011AH Performance: Data Rate vs Cable Length

10 Power Supply Recommendations

The DS90LV011AH driver is designed to operate from a single power supply with supply voltage in the range of 3.0 V to 3.6 V. In a typical application, a driver and a receiver may be on separate boards, or even separate equipment. In these cases, separate supplies would be used at each location. The expected ground potential difference between the driver power supply and the driver power supply would be less than |±1 V|. Board level and local device level bypass capacitance should be used.

11 Layout

11.1 Layout Guidelines

11.1.1 Microstrip vs. Stripline Topologies

As per the *LVDS Application and Data Handbook*, printed-circuit boards usually offer designers two transmission line options: Microstrip and stripline. Microstrips are traces on the outer layer of a PCB, as shown in 🗵 11-1.

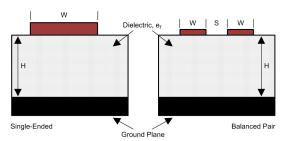


図 11-1. Microstrip Topology

On the other hand, striplines are traces between two ground planes. Striplines are less prone to emissions and susceptibility problems because the reference planes effectively shield the embedded traces. However, from the standpoint of high-speed transmission, juxtaposing two planes creates additional capacitance. TI recommends routing LVDS signals on microstrip transmission lines when possible. The PCB traces allow designers to specify the necessary tolerances for $Z_{\rm O}$ based on the overall noise budget and reflection allowances. Footnotes 1², 2³, and 3⁴ provide formulas for $Z_{\rm O}$ and $t_{\rm PD}$ for differential and single-ended traces. ² ³ ⁴

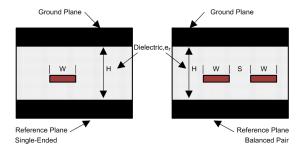


図 11-2. Stripline Topology

11.1.2 Dielectric Type and Board Construction

The speeds at which signals travel across the board dictates the choice of dielectric. FR-4, or equivalent, usually provides adequate performance for use with LVDS signals. If rise or fall times of LVCMOS/LVTTL signals are less than 500 ps, empirical results indicate that a material with a dielectric constant near 3.4, such as Rogers[™] 4350 or Nelco N4000-13 is better suited. Once the designer chooses the dielectric, there are several parameters pertaining to the board construction that can affect performance. The following set of guidelines were developed experimentally through several designs involving LVDS devices:

- Copper weight: 15 g or 1/2 oz start, plated to 30 g or 1 oz
- All exposed circuitry should be solder-plated (60/40) to 7.62 µm or 0.0003 in (minimum).
- Copper plating should be 25.4 µm or 0.001 in (minimum) in plated-through-holes.
- Solder mask over bare copper with solder hot-air leveling

Copyright © 2022 Texas Instruments Incorporated

² Howard Johnson & Martin Graham. 1993. High Speed Digital Design – A Handbook of Black Magic. Prentice Hall PRT. ISBN number 013395724.

Mark I. Montrose. 1996. Printed Circuit Board Design Techniques for EMC Compliance. IEEE Press. ISBN number 0780311310.

⁴ Clyde F. Coombs, Jr. Ed, Printed Circuits Handbook, McGraw Hill, ISBN number 0070127549.



11.1.3 Recommended Stack Layout

Following the choice of dielectrics and design specifications, the designer must decide how many levels to use in the stack. To reduce the LVCMOS/LVTTL to LVDS crosstalk, it is good practice to have at least two separate signal planes as shown in 211-3.

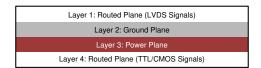


図 11-3. Four-Layer PCB Board

Note

The separation between layers 2 and 3 should be 127 μ m (0.005 in). By keeping the power and ground planes tightly coupled, the increased capacitance acts as a bypass for transients.

One of the most common stack configurations is the six-layer board, as shown in 🗵 11-4.

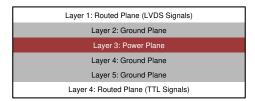


図 11-4. Six-Layer PCB Board

In this particular configuration, it is possible to isolate each signal layer from the power plane by at least one ground plane. The result is improved signal integrity, but fabrication is more expensive. Using the 6-layer board is preferable, because it offers the layout designer more flexibility in varying the distance between signal layers and referenced planes in addition to ensuring reference to a ground plane for signal layers 1 and 6.

11.1.4 Separation Between Traces

The separation between traces depends on several factors, but the amount of coupling that can be tolerated usually dictates the actual separation. Low-noise coupling requires close coupling between the differential pair of an LVDS link to benefit from the electromagnetic field cancellation. The traces should be $100-\Omega$ differential and thus coupled in the manner that best fits this requirement. In addition, differential pairs should have the same electrical length to ensure that they are balanced, thus minimizing problems with skew and signal reflection.

In the case of two adjacent single-ended traces, one should use the 3-W rule, which stipulates that the distance between two traces must be greater than two times the width of a single trace, or three times its width measured from trace center to trace center. This increased separation effectively reduces the potential for crosstalk. The same rule should be applied to the separation between adjacent LVDS differential pairs, whether the traces are edge-coupled or broad-side-coupled.

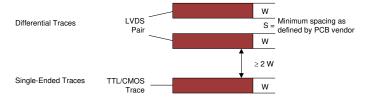


図 11-5. 3-W Rule for Single-Ended and Differential Traces (Top View)

Exercise caution when using autorouters, because they do not always account for all factors affecting crosstalk and signal reflection. For instance, it is best to avoid sharp 90° turns to prevent discontinuities in the signal path. Using successive 45° turns tends to minimize reflections.

Submit Document Feedback

11.1.5 Crosstalk and Ground Bounce Minimization

To reduce crosstalk, it is important to provide a return path to high-frequency currents that is as close to its originating trace as possible. A ground plane usually achieves this. Because the returning currents always choose the path of lowest inductance, they are most likely to return directly under the original trace, thus minimizing crosstalk. Lowering the area of the current loop lowers the potential for crosstalk. Traces kept as short as possible with an uninterrupted ground plane running beneath them emit the minimum amount of electromagnetic field strength. Discontinuities in the ground plane increase the return path inductance and should be avoided.

11.1.6 Decoupling

Each power or ground lead of a high-speed device should be connected to the PCB through a low inductance path. For best results, one or more vias are used to connect a power or ground pin to the nearby plane. TI recommends placing a via immediately adjacent to the pin to avoid adding trace inductance. Placing a power plane closer to the top of the board reduces the effective via length and its associated inductance.

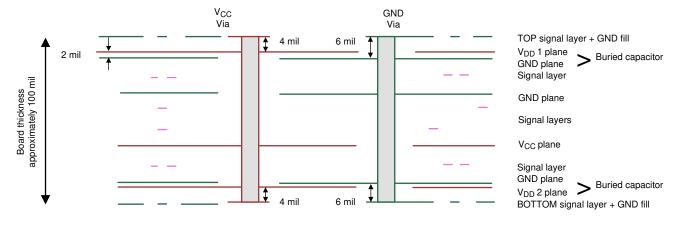


図 11-6. Low Inductance, High-Capacitance Power Connection

Bypass capacitors should be placed close to V_{DD} pins. They can be placed conveniently near the corners or underneath the package to minimize the loop area. This extends the useful frequency range of the added capacitance. Small-physical-size capacitors, such as 0402 or even 0201, or X7R surface-mount capacitors should be used to minimize body inductance of capacitors. Each bypass capacitor is connected to the power and ground plane through vias tangent to the pads of the capacitor as shown in \boxtimes 11-7(a).

Typical 12-Layer PCB

An X7R surface-mount capacitor of size 0402 has about 0.5 nH of body inductance. At frequencies above 30 MHz or so, X7R capacitors behave as low-impedance inductors. To extend the operating frequency range to a few hundred MHz, an array of different capacitor values like 100 pF, 1 nF, 0.03 μF, and 0.1 μF are commonly used in parallel. The most effective bypass capacitor can be built using sandwiched layers of power and ground at a separation of 2 to 3 mils. With a 2-mil FR4 dielectric, there is approximately 500 pF per square inch of PCB. Refer back to Figure 8 for some examples. Many high-speed devices provide a low-inductance GND connection on the backside of the package. This center dap must be connected to a ground plane through an array of vias. The via array reduces the effective inductance to ground and enhances the thermal performance of the small Surface Mount Technology (SMT) package. Placing vias around the perimeter of the dap connection ensures proper heat spreading and the lowest possible die temperature. Placing high-performance devices on opposing sides of the PCB using two GND planes (as shown in Σ 9-3) creates multiple paths for heat transfer. Often thermal PCB issues are the result of one device adding heat to another, resulting in a very high local temperature.

Multiple paths for heat transfer minimize this possibility. In many cases the GND dap that is so important for heat dissipation makes the optimal decoupling layout impossible to achieve due to insufficient pad-to-dap spacing as shown in \boxtimes 11-7(b). When this occurs, placing the decoupling capacitor on the backside of the board keeps the extra inductance to a minimum. It is important to place the V_{DD} via as close to the device pin as possible while still allowing for sufficient solder mask coverage. If the via is left open, solder may flow from the pad and into the via barrel. This will result in a poor solder connection.



図 11-7. Typical Decoupling Capacitor Layouts

At least two or three times the width of an individual trace should separate single-ended traces and differential pairs to minimize the potential for crosstalk. Single-ended traces that run in parallel for less than the wavelength of the rise or fall times usually have negligible crosstalk. Increase the spacing between signal paths for long parallel runs to reduce crosstalk. Boards with limited real estate can benefit from the staggered trace layout, as shown in \boxtimes 11-8.

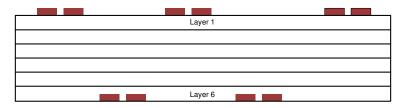


図 11-8. Staggered Trace Layout

This configuration lays out alternating signal traces on different layers. Thus, the horizontal separation between traces can be less than 2 or 3 times the width of individual traces. To ensure continuity in the ground signal path, TI recommends having an adjacent ground via for every signal via, as shown in 🗵 11-9. Note that vias create additional capacitance. For example, a typical via has a lumped capacitance effect of 1/2 pF to 1 pF in FR4.

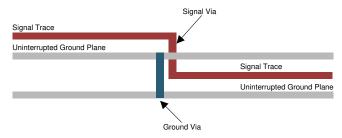


図 11-9. Ground Via Location (Side View)

Short and low-impedance connection of the device ground pins to the PCB ground plane reduces ground bounce. Holes and cutouts in the ground planes can adversely affect current return paths if they create discontinuities that increase returning current loop areas.

To minimize EMI problems, TI recommends avoiding discontinuities below a trace (for example, holes, slits, and so on) and keeping traces as short as possible. Zoning the board wisely by placing all similar functions in the same area, as opposed to mixing them together, helps reduce susceptibility issues.

Submit Document Feedback



11.2 Layout Example

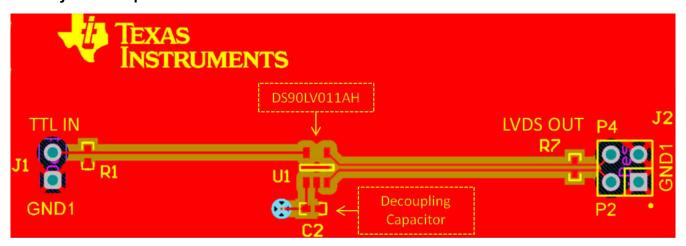


図 11-10. Example DS90LV011AH Layout



12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, LVDS Owner's Manual dseign guide
- Texas Instruments, AN-808 Long Transmission Lines and Data Signal Quality application note
- Texas Instruments, AN-977 LVDS Signal Quality: Jitter Measurements Using Eye Patterns Test Report #1
 application note
- Texas Instruments, AN-971 An Overview of LVDS Technology application note
- Texas Instruments, AN-916 A Practical Guide to Cable Selection application note
- Texas Instruments, AN-805 Calculating Power Dissipation for Differential Line Drivers application note
- Texas Instruments, AN-903 A Comparison of Differential Termination Techniques application note
- Texas Instruments, AN-1194 Failsafe Biasing of LVDS Interfaces application note

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 サポート・リソース

TI E2E[™] サポート・フォーラムは、エンジニアが検証済みの回答と設計に関するヒントをエキスパートから迅速かつ直接得ることができる場所です。既存の回答を検索したり、独自の質問をしたりすることで、設計で必要な支援を迅速に得ることができます。

リンクされているコンテンツは、該当する貢献者により、現状のまま提供されるものです。これらは TI の仕様を構成するものではなく、必ずしも TI の見解を反映したものではありません。TI の使用条件を参照してください。

12.4 Trademarks

Rogers[™] is a trademark of Rogers Corporation.

TI E2E[™] is a trademark of Texas Instruments.

すべての商標は、それぞれの所有者に帰属します。

12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

www.ti.com 23-May-2025

PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/ Ball material	MSL rating/ Peak reflow	Op temp (°C)	Part marking (6)
						(4)	(5)		
DS90LV011AHMF/NOPB	Active	Production	SOT-23 (DBV) 5	1000 SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	N04
DS90LV011AHMF/NOPB.A	Active	Production	SOT-23 (DBV) 5	1000 SMALL T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	N04
DS90LV011AHMFX/NO.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	N04
DS90LV011AHMFX/NOPB	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	N04

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE MATERIALS INFORMATION

www.ti.com 6-Jul-2025

TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DS90LV011AHMF/NOPB	SOT-23	DBV	5	1000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
DS90LV011AHMFX/ NOPB	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
DS90LV011AHMFX/ NOPB	SOT-23	DBV	5	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3

PACKAGE MATERIALS INFORMATION

www.ti.com 6-Jul-2025



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DS90LV011AHMF/NOPB	SOT-23	DBV	5	1000	210.0	185.0	35.0
DS90LV011AHMFX/NOPB	SOT-23	DBV	5	3000	210.0	185.0	35.0
DS90LV011AHMFX/NOPB	SOT-23	DBV	5	3000	210.0	185.0	35.0



SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



重要なお知らせと免責事項

テキサス・インスツルメンツは、技術データと信頼性データ (データシートを含みます)、設計リソース (リファレンス デザインを含みます)、アプリケーションや設計に関する各種アドバイス、Web ツール、安全性情報、その他のリソースを、欠陥が存在する可能性のある「現状のまま」提供しており、商品性および特定目的に対する適合性の黙示保証、第三者の知的財産権の非侵害保証を含むいかなる保証も、明示的または黙示的にかかわらず拒否します。

これらのリソースは、 テキサス・インスツルメンツ製品を使用する設計の経験を積んだ開発者への提供を意図したものです。(1) お客様のアプリケーションに適した テキサス・インスツルメンツ製品の選定、(2) お客様のアプリケーションに該当する各種規格や、その他のあらゆる安全性、セキュリティ、規制、または他の要件への確実な適合に関する責任を、お客様のみが単独で負うものとします。

上記の各種リソースは、予告なく変更される可能性があります。これらのリソースは、リソースで説明されている テキサス・インスツルメンツ製品を使用するアプリケーションの開発の目的でのみ、 テキサス・インスツルメンツはその使用をお客様に許諾します。これらのリソースに関して、他の目的で複製することや掲載することは禁止されています。 テキサス・インスツルメンツや第三者の知的財産権のライセンスが付与されている訳ではありません。お客様は、これらのリソースを自身で使用した結果発生するあらゆる申し立て、損害、費用、損失、責任について、 テキサス・インスツルメンツおよびその代理人を完全に補償するものとし、 テキサス・インスツルメンツは一切の責任を拒否します。

テキサス・インスツルメンツの製品は、 テキサス・インスツルメンツの販売条件、または ti.com やかかる テキサス・インスツルメンツ 製品の関連資料などのいずれかを通じて提供する適用可能な条項の下で提供されています。 テキサス・インスツルメンツがこれらのリソ 一スを提供することは、適用される テキサス・インスツルメンツの保証または他の保証の放棄の拡大や変更を意味するものではありません。

お客様がいかなる追加条項または代替条項を提案した場合でも、 テキサス・インスツルメンツはそれらに異議を唱え、拒否します。

郵送先住所: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2025, Texas Instruments Incorporated